Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A fabrication method of a semiconductor integrated circuit device, comprising the step of using a first photomask which has, as a blocker against an exposure light, an organic material containing an organic photosensitive resin ~~and~~ or a second photomask which has, as a blocker against an exposure light, a metal film, the first or second photomask being selected depending on ~~the~~ a production amount or fabrication step of the semiconductor integrated circuit device.

2. (Canceled).

3. (Currently Amended) A fabrication method of a semiconductor integrated circuit device, comprising the steps of:

(a) judging whether ~~the~~ a production amount of the semiconductor integration circuit device exceeds a predetermined threshold production amount or not; and

(b) when the production amount of the semiconductor integrated circuit device does not exceed the predetermined threshold value, using, upon exposure treatment, a photomask which has, as a blocker against an exposure light, an organic material containing an organic photosensitive resin film ~~upon exposure treatment~~.

4. (Currently Amended) A fabrication method of a semiconductor integrated circuit device according to claim 3, further comprising ~~the~~ a step of using a photomask which has, as a blocker against an exposure light, a metal film upon exposure treatment when the production amount of the semiconductor integrated

circuit device is expanded to exceed the threshold value.

5. (Currently Amended) A fabrication method of a semiconductor integrated circuit device, comprising the steps of:

(a) judging whether ~~the~~ a production amount of the semiconductor integration circuit device exceeds a predetermined threshold production amount or not;

(b) when the production amount of the semiconductor integrated circuit device exceeds the threshold value, judging whether ~~the~~ a function of the semiconductor integrated circuit device has been determined or not;

(c) when the function has not been determined, using, upon exposure treatment a photomask which has, as a blocker against an exposure light, an organic material containing an organic photosensitive resin film ~~upon exposure treatment~~.

6. (Currently Amended) A fabrication method of a semiconductor integrated circuit device according to claim 5, further comprising ~~the~~ a step of using, upon exposure treatment when the function of the semiconductor integrated circuit device is determined, a photomask which has, as a blocker against an exposure light, a metal film ~~upon exposure treatment in a stage when the function of the semiconductor integrated circuit device is determined~~.

7. (Currently Amended) A fabrication method of a semiconductor integrated circuit device according to claim 5, further comprising ~~the~~ a step of using, upon exposure treatment when the function of the semiconductor integrated circuit device has been determined, a photomask which has, as a blocker against an exposure light, a metal film ~~upon exposure treatment when the function of the semiconductor integrated circuit device has been determined~~.

8. (Currently Amended) A fabrication method of a semiconductor integrated circuit device, comprising ~~the~~ a step of using, upon exposure treatment prior to a

mass production step, a photomask, as a blocker against an exposure light, an organic material containing an organic photosensitive resin ~~upon exposure treatment prior to a mass production step~~.

9. (Currently Amended) A fabrication method of a semiconductor integrated circuit device, comprising the step of using, upon exposure treatment prior to a mass production step, a first photomask which has, as a blocker against an exposure light, an organic material containing an organic photosensitive resin ~~upon exposure treatment prior to a mass production step~~, and in the mass production step, using, upon exposure treatment, a second photomask which has, as a blocker against an exposure light, a metal film ~~upon exposure treatment~~.

10. (Currently Amended) A fabrication method of a semiconductor integrated circuit device, comprising the step of using, upon exposure treatment in a step of forming patterns relating to a constitution at a logic circuit, a first photomask which has, as a blocker against an exposure light, an organic material containing an organic photosensitive resin ~~upon exposure treatment in a step of forming patterns relating to the constitution of a logic circuit~~, ~~while~~ and using, upon exposure treatment in a step of forming patterns relating to a unit cell, a second photomask which has, as a blocker against an exposure light, a metal film ~~upon exposure treatment in a step of forming patterns relating to a unit cell~~.

11. (Currently Amended) A fabrication method of a semiconductor integrated circuit device, comprising the steps of:

(a) using, upon exposure treatment for forming patterns relating to a constitution of a logic circuit prior to a mass production step of the semiconductor integrated circuit device, a first photomask having, as a blocker against an exposure light, an organic material containing an organic photosensitive resin ~~upon exposure~~

~~treatment for forming patterns relating to the constitution of a logic circuit prior to a mass production step of the semiconductor integrated circuit device,~~

(b) using, upon exposure treatment for forming patterns relating a constitution of the logic circuit in the mass production step of the semiconductor integrated circuit device, a second photomask having a metal as a blocker against an exposure light ~~upon exposure treatment for forming patterns relating the constitution of the logic circuit in the mass production step of the semiconductor integrated circuit device,~~ and

(c) using ~~the second~~, upon exposure treatment for forming patterns relating to a unit cell prior to the mass production step and in the mass production step, a third photomask having a metal as a blocker against an exposure light ~~upon exposure treatment for forming patterns relating to a unit cell prior to the mass production step and in the mass production step~~.

12. A fabrication method of a semiconductor integrated circuit device having an ROM, comprising the steps of using, upon exposure treatment for forming patterns relating to data writing of the ROM, a first photomask having, as a blocker against an exposure light, an organic material containing an organic photosensitive resin ~~upon exposure treatment for forming patterns relating to data writing of the ROM~~; and using, upon exposure treatment for forming patterns other than those relating to the data writing, a second photomask having a metal as a blocker against an exposure light ~~upon exposure treatment for forming patterns other than those relating to the data writing~~.

13. A fabrication method of a semiconductor integrated circuit device having an ROM, comprising the steps of:

(a) using, upon exposure treatment for forming patterns relating to data writing

of the ROM prior to a mass production step of the semiconductor integrated circuit device, a first photomask having, as a blocker against an exposure light, an organic material containing an organic photosensitive resin ~~upon exposure treatment for forming patterns relating to data writing of the ROM prior to a mass production step of the semiconductor integrated circuit device~~,

(b) using, upon exposure treatment for forming patterns relating to data writing of the ROM in the mass production step of the semiconductor integrated circuit device, a second photomask having a metal as a blocker against an exposure light ~~upon exposure treatment for forming patterns relating to data writing of the ROM in the mass production step of the semiconductor integrated circuit device~~; and

(c) using, upon exposure treatment for forming patterns other than those relating to data writing of the ROM prior to the mass production step and in the mass production step, the second photomask having a metal as a blocker against an exposure light ~~upon exposure treatment for forming patterns other than those relating to data writing of the ROM prior to the mass production step and in the mass production step~~.

14. (Canceled).

15. A fabrication method of a semiconductor integrated circuit device, comprising, upon forming patterns of the semiconductor integrated circuit device, properly using one of:

(a) exposure treatment using a first photomask having, as a blocker against an exposure light, an organic material containing an organic photosensitive resin;

(b) another exposure treatment using a second photomask having a metal film as a blocker against an exposure light; and

(c) direct writing treatment using an energy beam.

16. A fabrication method of a semiconductor integrated circuit device according to claim 15, comprising the steps of:

judging whether the using amount of the first or second photomask exceeds a predetermined threshold using amount or not;

judging whether the first photomask is usable or not when the using amount of the first photomask is less than the threshold value, and

carrying out exposure treatment with the first photomask when the first photomask is usable while carrying out direct writing treatment using the energy beam when the first photomask is unusable.

17. A fabrication method of a semiconductor integrated circuit device according to claim 15, comprising the steps of:

judging whether the using amount of the first or second photomask exceeds a predetermined threshold using amount or not;

judging whether the second photomask is usable or not when the using amount of the second photomask exceeds the threshold value,

carrying out exposure treatment with the second photomask when the second photomask is usable,

judging whether the first photomask is usable or not when the second photomask is unusable,

carrying out exposure treatment with the first photomask when the first photomask is usable, and

carrying out direct writing treatment with the energy beam when the second and first photomasks ~~is~~are unusable.

18. A fabrication method of a semiconductor integrated circuit device, comprising the steps of:

(a) forming a first photomask having, as a blocker against an exposure light, an organic material containing an organic photosensitive resin on a semiconductor-integrated-circuit-device evaluator's side;

(b) transferring a predetermined pattern onto a semiconductor wafer by exposure treatment with the first photomask, on a semiconductor-integrated-circuit-device maker's side; and

(c) evaluating the semiconductor wafer to which the predetermined pattern has been transferred, on the semiconductor-integrated-circuit-device evaluator's side.

19. A fabrication method of a semiconductor integrated circuit device, comprising the steps of:

(a) using a photomask having a metal film as a blocker against an exposure light upon exposure treatment in a mass production step of the semiconductor integrated circuit device;

(b) discarding the photomask having a metal film as a blocker against an exposure light after completion of the mass production step of the semiconductor integrated circuit device; and

(c) using another photomask having, as a blocker against an exposure light, an organic material containing an organic photosensitive resin upon exposure treatment in reproduction of the semiconductor integrated circuit device.

20. A fabrication method of a semiconductor integrated circuit device according to claim 19, wherein upon reproduction of the semiconductor integrated circuit device, in the stage when the production amount exceeds a predetermined threshold production amount, a photomask having a metal film as a blocker against an exposure light is used instead of the another photomask having, as a blocker

against an exposure light, an organic material containing an organic photosensitive resin upon exposure treatment.

21. A fabrication method of a semiconductor integrated circuit device, comprising the steps of:

(a) using a first photomask having, as a blocker against an exposure light, an organic material containing an organic photosensitive resin upon exposure treatment prior to a mass production step of the semiconductor integrated circuit device; and

(b) using a second photomask having a metal film as a blocker against an exposure light upon exposure treatment in the mass production step of the semiconductor integrated circuit device,

wherein said first photomask has a plurality of semiconductor chip transfer regions disposed thereon, and

patterns having data of the semiconductor integrated circuit device which are different from each other are disposed in the transfer regions, respectively.

22. A fabrication method of a semiconductor integrated circuit device according to claim 21, wherein said second photomask has a plurality of semiconductor chip transfer regions disposed thereon and patterns having the same data of the semiconductor integrated circuit device selected in an evaluation step are disposed in the transfer regions.

23. (Canceled).

24. (Canceled).

25. (Canceled).